

SILICON DIODES . . . cont'd

Case Style — D0-7

TYPE	MAX. PEAK REVERSE VOLTAGE (volts)	MAX. FORWARD VOLTAGE (volts)	FORWARD CURRENT (mA)	REVERSE CURRENT (μ A) 25°C	REVERSE CURRENT (μ A) 150°C	REVERSE VOLTAGE (volts)	CAPACITANCE (pF)	RECOVERY TIME (μ sec)	POWER DISSIPATION (mW)
1N462A	70	1.0	100	.5	30	60	—	—	250 (A)
1N463	200	1.0	1	.5	30	175	—	—	250 (A)
1N463A	200	1.0	100	.5	30	175	—	—	250 (A)
1N464	150	1.0	3	.5	30	125	—	—	250 (A)
1N464A	150	1.0	100	.5	30	125	—	—	250 (A)
1N482	40	1.1	100	.25	30	30	—	—	250 (A)
1N482A	40	1.0	100	.025	15	30	—	—	250 (A)
1N482B	40	1.0	100	.025	5	30	—	—	250 (A)
1N483	80	1.1	100	.25	30	60	—	—	250 (A)
1N483A	80	1.0	100	.025	15	60	—	—	250 (A)
1N483B*	80	1.0	100	.025	5	60	—	—	250 (A)
1N484	150	1.1	100	.25	30	125	—	—	250 (A)
1N484A	150	1.0	100	.025	15	125	—	—	250 (A)
1N484B	150	1.0	100	.025	5	125	—	—	250 (A)
1N485	200	1.1	100	.25	30	175	—	—	250 (A)
1N485A	200	1.0	100	.025	15	175	—	—	250 (A)
1N485B*	200	1.0	100	.025	5	175	—	—	250 (A)
1N486	250	1.1	100	.25	50	225	—	—	250 (A)
1N486A	250	1.0	100	.05	25	225	—	—	250 (A)
1N486B*	250	1.0	100	.05	10	225	—	—	250 (A)
1N487	330	1.1	100	.25	50	300	—	—	250 (A)
1N487A	330	1.0	100	.1	25	300	—	—	250 (A)
1N488	420	1.1	100	.25	50	380	—	—	250 (A)
1N488A	420	1.0	100	.1	25	380	—	—	250 (A)
1N625	35	1.5	4	1.0	30	20	—	1.0	200 (P)
1N626	50	1.5	4	1.0	30	35	—	1.0	200 (P)
1N627	100	1.5	4	1.0	30	75	—	1.0	200 (P)
1N628	150	1.5	4	1.0	30	125	—	1.0	200 (P)
1N629	200	1.5	4	1.0	30	175	—	1.0	200 (P)
1N643*	200	1	10	.025	5 (1)	10	—	.3	200 (P)
1N645*	275 (2)	1	400	.2	15 (2)	275	—	—	400 (A)
1N646	360 (2)	1	400	.2	15 (2)	360	—	—	400 (A)
1N647	480 (2)	1	400	.2	20 (2)	480	—	—	400 (A)
1N648	600 (2)	1	400	.2	20 (2)	600	—	—	400 (A)
1N649	720 (2)	1	400	.2	25 (2)	720	—	—	400 (A)
1N658*	120	1	100	.05	25	50	—	.3	200 (P)
1N659	55	1	6	5	25 (1)	50	—	.3	200 (P)
1N660*	110	1	6	5	50 (1)	100	—	.3	200 (P)
1N661*	220	1	6	10	100 (1)	200	—	.3	200 (P)
1N662*	100	1	10	1	20 (1)	10	—	.5	200 (P)
1N663*	100	1	100	5	50 (1)	75	—	.5	200 (P)
1N673	350	1	250	1	—	300	—	—	400 (A)
1N676	115	1	200	1.0	—	115	—	—	400 (A)
1N677	115	1	400	1.0	—	115	—	—	400 (A)
1N678	230	1	200	1.0	—	230	—	—	400 (A)
1N679	230	1	400	1.0	—	230	—	—	400 (A)
1N681	340	1	200	1.0	—	340	—	—	400 (A)
1N682	340	1	400	1.0	—	340	—	—	400 (A)
1N683	455	1	200	1.0	—	455	—	—	400 (A)
1N684	455	1	400	1.0	—	455	—	—	400 (A)
1N685	565	1	200	1.0	—	565	—	—	400 (A)
1N688	565	1	400	1.0	—	565	—	—	400 (A)
1N687	680	1	200	1.0	—	680	—	—	400 (A)
1N689	680	1	400	1.0	—	680	—	—	400 (A)

Notes: * Available in mll. version (A) Silicon alloy construction (P) Silicon planar construction (1) +125°C (2) +100°C

SILICON DIODES . . . cont'd

Case Style — DO-7

TYPE	MAX. PEAK REVERSE VOLTAGE (volts)	MAX. FORWARD VOLTAGE (volts)	FORWARD CURRENT (mA)	REVERSE CURRENT (μ A) 25°C	REVERSE CURRENT (μ A) 150°C	REVERSE VOLTAGE (volts)	CAPACITANCE (pF)	RECOVERY TIME (μ sec)	POWER DISSIPATION (mW)
1N698	40	1	10	.015	20	20	—	.005	250 (P)
1N697	120	1	250	1	800	50	25	.100	250 (P)
1N806	110	1.0	4	.5	50 (1)	100	—	.3	200 (P)
1N807	200	1.0	4	.5	50 (1)	175	—	.3	200 (P)
1N811	20	1.0	1	1.0	10 (1)	10	—	.25	150 (P)
1N812	30	1.0	2	.1	10 (1)	10	—	.25	150 (P)
1N813	15	1.0	5	.5	10 (1)	5	—	.25	150 (P)
1N814	40	1.0	2	.1	10 (1)	20	—	.25	150 (P)
1N815	15	1.5	100	.5	10 (1)	5	—	.25	150 (P)
1N816*	—	0.64 $\pm$ 10%	1	.1	—	4	—	—	250 (A)
1N846	50	1	200	20	—	35	—	—	400 (A)
1N847	100	1	200	20	—	70	—	—	400 (A)
1N848	200	1	200	20	—	140	—	—	400 (A)
1N849	300	1	200	20	—	210	—	—	400 (A)
1N850	400	1	200	20	—	280	—	—	400 (A)
1N851	500	1	200	20	—	350	—	—	400 (A)
1N852	600	1	200	20	—	420	—	—	400 (A)
1N853	700	1	200	20	—	490	—	—	400 (A)
1N854	800	1	200	20	—	560	—	—	400 (A)
1N855	900	1	200	20	—	630	—	—	400 (A)
1N856	1000	1	200	20	—	700	—	—	400 (A)
1N857	50	1	150	20	—	35	—	—	400 (A)
1N858	100	1	150	20	—	70	—	—	400 (A)
1N859	200	1	150	20	—	140	—	—	400 (A)
1N860	300	1	150	20	—	210	—	—	400 (A)
1N861	400	1	150	20	—	280	—	—	400 (A)
1N862	500	1	150	20	—	350	—	—	400 (A)
1N863	600	1	150	20	—	420	—	—	400 (A)
1N864	700	1	150	20	—	490	—	—	400 (A)
1N865	800	1	150	20	—	560	—	—	400 (A)
1N866	900	1	150	20	—	630	—	—	400 (A)
1N867	1000	1	150	20	—	700	—	—	400 (A)
1N868	50	1	150	20	—	35	—	—	400 (A)
1N869	100	1	100	20	—	100	—	—	400 (A)
1N870	200	1	100	20	—	140	—	—	400 (A)
1N872	400 @ 20 μ A	1	300	—	—	—	—	—	400 (A)
1N873	500	1	100	20	—	350	—	—	400 (A)
1N874	—	1	100	100	—	600	—	—	400 (A)
1N875	700 @ 20	1	100	—	—	—	—	—	400 (A)
1N876	800	1	100	20	—	560	—	—	400 (A)
1N877	900	1	100	20	—	630	—	—	400 (A)
1N878	1000	1	100	20	—	700	—	—	400 (A)
1N879	—	1	200	20	—	50	—	—	400 (A)
1N880	100	1	50	20	—	70	—	—	400 (A)
1N881	200	1	50	20	—	140	—	—	400 (A)
1N882	300	1	50	20	—	210	—	—	400 (A)
1N883	400	1	50	20	—	280	—	—	400 (A)
1N884	500	1	50	20	—	350	—	—	400 (A)
1N886	—	1	200	20	—	700	—	—	400 (A)
1N887	800	1	50	20	—	560	—	—	400 (A)
1N888	900 @ 20 μ A	1	200	—	—	—	—	—	400 (A)
1N889	1000	1	400	20	—	700	—	—	400 (A)

Notes: * Available in mil. version (A) Silicon alloy construction (P) Silicon planar construction (1) -125°C

SILICON DIODES . . . cont'd Case Style — DO-7

TYPE	MAX. PEAK REVERSE VOLTAGE (volts)	MAX. FORWARD VOLTAGE (volts)	FORWARD CURRENT (mA)	REVERSE CURRENT (μ A) 25°C	REVERSE CURRENT (μ A) 150°C	REVERSE VOLTAGE (volts)	CAPACITANCE (pF)	RECOVERY TIME (μ sec)	POWER DISSIPATION (mW)
1N891	60	1	50	.1	25 (3)	50	10	.3	250 (P)
1N903	—	1	10	.1	10 (2)	40	—	.4	250 (P)
1N903A	—	1	20	.1	10 (2)	40	—	.4	250 (P)
1N904	—	1	10	.1	10 (2)	30	1	.004	250 (P)
1N904A	40	1	20	.1	10 (2)	30	1	.004	250 (P)
1N905	—	1	10	.1	10 (2)	20	1	.004	250 (P)
1N905A	30	1	20	.1	10 (2)	20	1	.004	250 (P)
1N906	—	1	10	.1	10 (2)	20	2.5	.004	250 (P)
1N906A	—	1	20	.1	10 (2)	20	2.5	.004	250 (P)
1N907	—	1	10	.1	10 (2)	30	2.5	.004	250 (P)
1N907A	—	1	20	.1	10 (2)	30	2.5	.004	250 (P)
1N908	—	1	10	.1	10 (2)	40	2.5	.004	250 (P)
1N908A	—	1	20	.1	10 (2)	40	2.5	.004	250 (P)
1N914	100	1	10	.025	50	20	4	.004	250 (P)
1N914A	100	1	20	.025	50	20	4	.004	250 (P)
1N914B	100	1	100	.025	50	20	4	.004	250 (P)
1N916	100	1	10	.025	50	20	2	.004	250 (P)
1N916A	100	1	20	.025	50	20	2	.004	250 (P)
1N916B	75	1	20	.025	50	20	2	.004	250 (P)
1N919	200	1	100	.5	25 (2)	150	—	.3	200 (P)
1N925	40	1	5	.1	20 (2)	10	4	.15	250 (P)
1N926	40	1	5	.1	10 (2)	10	4	.15	250 (P)
1N927	65	1	10	.1	10 (2)	10	4	.15	250 (P)
1N928	—	1	10	.1	10 (2)	10/100	—	.15	250 (P)
1N948	40	1.5	100	.25	20	30	—	1	250 (P)
1N993	8	1.5	10	1	—	6	—	.004	50 (P)
1N3062	75 @ 5 μ A	1	20	.1	100	50	1	.002	250 (P)
1N3063	75 @ 5 μ A	.505 min./575 max. .550 min./650 max. .610 min./710 max.	.25 1 2	.1	100	50	2	.004	250 (P)
1N3064*	75 @ 5 μ A	.700 min./850 max.	10	—	—	—	—	—	—
1N3065	75 @ 5 μ A	.460 min./530 max. .570 min./670 max. .730 min./880 max.	10 1 10	.1 — —	100 100 —	50 50 —	2 1.5 —	.004 .004 —	250 (P) 250 (P) —
1N3066	—	.800 min./1.00 max.	20	—	—	—	—	—	—
1N3068	75 @ 5 μ A	1	10	.1	100	50	1	.002	250 (P)
1N3067	30 @ 5 μ A	1	5	.1	100	20	4	.004	250 (P)
1N3068	30 @ 5 μ A	1	5	.1	100	20	6	.050	250 (P)
1N3069	65 @ 5 μ A	1	50	.1	100	50	6	.050	250 (P)
1N3070	200	1	100	.1	100	175	5	.050	250 (P)
1N3071	200	.530 min./630 max. .640 min./740 max. .760 min./920 max. .800 min./1.00 max.	1 10 50 100	.1 — — —	100 — — —	150 — — —	5 — — —	.050 — — —	250 (P) — — —
1N3257	100	1	30	.025	25	20/50	2	.003	250 (P)
1N3258	100	1	100	.025	25	20/50	4	.004	250 (P)
1N3600*	—	.54 min./62 max. .66 min./74 max. .76 min./86 max. .82 min./92 max. .87 min./1.0 max.	1 10 50 100 200	.1 — — — —	100 — — — —	50 — — — —	2.5 — — — —	.004 — — — —	250 (P) — — — —
1N3604	75 @ 5 μ A	1	50	.05	50	50	2	.004	250 (P)
1N3605	40 @ 5 μ A	.490 min./550 max. .530 min./590 max. .590 min./670 max. .620 min./700 max. .700 min./810 max.	.1 1 2 2 10	.05 — — — —	50 — — — —	30 — — — —	2 — — — —	.004 — — — —	250 (P) — — — —

Notes: * Available in mil. version (A) Silicon alloy construction (P) Silicon planar construction (2) +100°C (3) +50°C

GENERAL DIODE CORP

86 DE 3869720 0000341 3

SILICON DIODES . . . cont'd

Case Style — D0-7

TYPE	MAX PEAK REVERSE VOLTAGE (volts)	MAX FORWARD VOLTAGE (volts)	FORWARD CURRENT (mA)	REVERSE CURRENT (μ A) 25°C	REVERSE CURRENT (μ A) 150°C	REVERSE VOLTAGE (volts)	CAPACITANCE (pF)	RECOVERY TIME (μ sec)	POWER DISSIPATION (mW)
1N3608	75 @ 5 μ a	.750 min./1.880 max. .490 min./1.550 max. .530 min./1.590 max. .590 min./1.670 max. .620 min./1.700 max.	20 .1 .25 1 2	— — — — —	50 — — — —	50 — — — —	— — — — —	.004 — — — —	250 (P)
1N3653	100	.700 min./1.810 max. .740 min./1.880 max.	10 20	— —	— —	— —	— —	— —	— —
1N3731	100	1	400	.025	25	75	4	.004	250 (P)
1N4009	35 @ 5 μ a	1	100	.05	50	50	2	.003	250 (P)
1N4087	—	.700 min./1.750 max. .975 max.	5 30	.09 —	100 —	50 —	1.8 —	.030 —	250 (P)
1N4082	50 @ 10 μ a	1	5	1	—	10	10	—	250 (A)
SG22	—	.64 $\pm$ 10%	1	.1	5 (4)	20	—	—	250 (A)
SG22	—	1	100	—	—	—	—	—	—
SG211	80	1.5	5	.25	20 (2)	60	—	.3	200 (P)
SG212	150	1.5	5	.25	20 (2)	125	—	.3	200 (P)
SG213	200	1.5	5	.25	50 (2)	175	—	.3	200 (P)
SG215	40	1.5	5	.25	20 (2)	30	—	1	200 (P)
SG218	80	1.5	5	.25	20 (2)	60	—	1	200 (P)
SG217	150	1.5	5	.25	20 (2)	125	—	1	200 (P)
SG219	200	1.5	5	.25	50 (2)	175	—	1	200 (P)
SG221	80	1.5	30	.25	20 (2)	60	—	.5	200 (P)
SG222	150	1.5	30	.25	20 (2)	125	—	.5	200 (P)
SG223	200	1.5	30	.25	50 (2)	175	—	.5	200 (P)
SG225	40	1.5	100	.25	20 (2)	30	—	1	200 (P)
SG226	80	1.5	100	.25	20 (2)	60	—	1	200 (P)
SG227	150	1.5	100	.25	20 (2)	125	—	1	200 (P)
SG228	200	1.5	100	.25	50 (2)	175	—	1	200 (P)
SG5000	100 @ 5 μ a	1	200	.25	100	75	2	.004	400 (P)
—	—	.47 min./1.53 max.	.25	—	—	—	—	—	—
—	—	.52 min./1.60 max.	1	—	—	—	—	—	—
—	—	.64 min./1.72 max.	10	—	—	—	—	—	—
SG5100	50 @ 5 μ a	.67 min./1.77 max.	20	—	—	—	—	—	—
—	—	1	400	.25	100	30	4	.004	400 (P)
—	—	.47 min./1.53 max.	.25	—	—	—	—	—	—
—	—	.52 min./1.60 max.	1	—	—	—	—	—	—
—	—	.64 min./1.72 max.	10	—	—	—	—	—	—
SG5200	75 @ 5 μ a	.67 min./1.77 max.	20	—	—	—	—	—	—
—	—	1	400	.25	100	50	4	.004	400 (P)
—	—	.47 min./1.53 max.	.25	—	—	—	—	—	—
—	—	.52 min./1.60 max.	1	—	—	—	—	—	—
—	—	.64 min./1.72 max.	10	—	—	—	—	—	—
—	—	.67 min./1.77 max.	20	—	—	—	—	—	—
SG5250	50 @ 5 μ a	.90	100	.025	100	20	6	.004	200 (P)
SG5260	75 @ 5 μ a	.90	100	.025	100	20	6	.004	200 (P)
SG5270	100 @ 5 μ a	.90	100	.10	100	75	6	.004	200 (P)
SG5300	100 @ 5 μ a	1	300	.25	100	75	2	.004	400 (P)
—	—	.47 min./1.53 max.	.25	—	—	—	—	—	—
—	—	.52 min./1.60 max.	1	—	—	—	—	—	—
—	—	.64 min./1.72 max.	10	—	—	—	—	—	—
—	—	.67 min./1.77 max.	20	—	—	—	—	—	—
SG5400	150 @ 5 μ a	1	200	.25	100	100	2	.004	400 (P)
—	—	.47 min./1.53 max.	.25	—	—	—	—	—	—
—	—	.52 min./1.60 max.	1	—	—	—	—	—	—
—	—	.64 min./1.72 max.	10	—	—	—	—	—	—
—	—	.67 min./1.77 max.	20	—	—	—	—	—	—
SG5800	30 @ 5 μ a	.89 min./1.1 max. .81 min./1.95 max. .76 min./1.88 max. .64 min./1.74 max. .52 min./1.61 max. .42 min./1.50 max.	50 20 10 1 .1 .01	50 μ a — — — — —	50 μ a — — — — —	15 — — — — —	.75 — — — — —	700/sec — — — — —	200mW — — — — —

Notes: (A) Silicon alloy construction (P) Silicon planar construction (2) +100°C

SILICON DIODES . . . cont'd

Case Style — Do-35 Whiskerless

TYPE	MAX. PEAK REVERSE VOLTAGE (volts)	MAX. FORWARD VOLTAGE (volts)	FORWARD CURRENT (mA)	REVERSE CURRENT (μ A) 25°C	REVERSE CURRENT (μ A) 150°C	REVERSE VOLTAGE (volts)	CAPACITANCE (pF)	RECOVERY TIME (μ sec)	POWER DISSIPATION (mW)
1N4148	100	1	10	.025	50	20	4	1	400 (P)
1N4149	100	1	10	.025	50	20	2	1	400 (P)
1N4150	50	.54 min./ .62 max.	1	.1	100	50	2.5	1	400 (P)
		.66 min./ .74 max.	10	—	—	—	—	—	—
		.76 min./ .86 max.	50	—	—	—	—	—	—
		.82 min./ .92 max.	100	—	—	—	—	—	—
		.87 min./ 1.0 max.	200	—	—	—	—	—	—
1N4151	75	1	50	.05	50	50	2	1	400 (P)
1N4152	40	.490 min./ .550 max.	.1	.05	50	30	2	.00	400 (P)
		.530 min./ .590 max.	.25	—	—	—	—	—	—
		.590 min./ .670 max.	1	—	—	—	—	—	—
		.620 min./ .700 max.	2	—	—	—	—	—	—
		.700 min./ .810 max.	10	—	—	—	—	—	—
		.740 min./ .880 max.	20	—	—	—	—	—	—
1N4153*	75	.490 min./ .550 max.	.1	.05	50	50	2	.00	400 (P)
		.530 min./ .590 max.	.25	—	—	—	—	—	—
		.590 min./ .670 max.	1	—	—	—	—	—	—
		.620 min./ .700 max.	2	—	—	—	—	—	—
		.700 min./ .810 max.	10	—	—	—	—	—	—
		.740 min./ .880 max.	20	—	—	—	—	—	—
1N4154	35	1	30	.1	100	25	4	—	400 (P)
1N4305	75	.505 min./ .575 max.	.25	.1	100	50	2	—	400 (P)
		.550 min./ .650 max.	1	—	—	—	—	—	—
		.610 min./ .710 max.	2	—	—	—	—	—	—
		.700 min./ .850 max.	10	—	—	—	—	—	—
1N4448	100	1.0	20	.025	.05	20	4.0	4.0	250
1N4447	100	1.0	20	.025	50	20	2.0	4.0	250
1N4448	100	1.0	100	.025	50	20	4.0	4.0	250
1N4449	100	1.0	30	.025	50	20	2.0	4.0	250
1N4454	75 @ 5uA	1.0	10	.1	100	50	2.0	4.0	500
1N4608	85 @ 100uA	1.1	250	⊙	25 @ 100°C	50	2.5	4.0	500

Notes: (A) Silicon alloy construction (P) Silicon planar construction (4) +70°C

Case Style Do-35

SG9150	30	1.0	10	1.0	100	25	10	.010	250
SG9200	100	1.0	200	.25	100	30	2	.004	400
SG9210	50	1.0	400	.25	100	75	4	.004	400
SG9220	75	1.0	400	.25	100	50	4	.004	400
SG9230	100	1.0	300	.25	100	75	2	.004	400
SG9240	150	1.0	200	.25	100	100	2	.004	400
SG9600	50	.87 min./ 1.0 max.	200	.1	100	50	2.5	.004	500

Case Style — Do-34 Whiskerless

1N4531	100	1.0	10	.025	50	20	4	.004	250
1N4532	75	1.0	10	.1	100	50	2	.004	250
1N4533	40	.7 min./ .81 max.	10	.05	50	30	2	.004	250
1N4534	75	.7 min./ .81 max.	10	.05	50	50	2	.004	250
1N4538	35	1.0	30	.1	100	25	4	.004	250
1N5317	80	1.1	300	.1	100	55	2.5	.004	400
1N5318	75	1.0	200	.1	100	50	2.5	.004	400
1N5319	40	1.0	100	.1	100*	25	3.5	.004	400

* Measured at 100°C